

**Amendments to the Claims:**

**Listing of Claims:**

- 5 Claim 1 (Currently amended) A process for depositing silicon nitride films on wafers, comprising:
- providing a chemical vapor deposition (CVD) system comprising a tubular furnace, at least one BTBAS (bis t-ButylaminoSilane) supply piping line connected to a base portion of said tubular furnace, an exhaust piping line connected to an upper portion of said tubular furnace, a bypass line connecting said BTBAS supply piping line with said exhaust piping line, and a vacuum pump connected to said exhaust piping line, wherein
- 10 said bypass line is initially interrupted;
- placing a batch of wafers into a tube of said tubular furnace;
- flowing nitrogen-containing gas into said tube;
- flowing BTBAS into said tube through said BTBAS supply piping line and said
- 15 vacuum pump maintaining pressure in said tube in a range of between about 0.1 Torr and 3 Torr;
- performing a silicon nitride deposition process in said tube to deposit a BTBAS-based silicon nitride film on said wafers;
- upon completion of said silicon nitride deposition process, interrupting said BTBAS
- 20 supply piping line and opening said initially interrupted bypass line to evacuating said BTBAS from said BTBAS supply piping line between said tubular furnace and a BTBAS supply source by way of said bypass line instead of by way of said tubular furnace; and
- removing said batch of wafers.
- 25 Claim 2 (Original) The process for depositing silicon nitride films on wafers according to claim 1 wherein after removing said batch of wafers, the process further comprises flowing cleaning gas into said tube.

Claim 3 (Original) The process for depositing silicon nitride films on wafers according to claim 2 wherein said cleaning gas comprises  $\text{ClF}_3$ .

5 Claim 4 (Original) The process for depositing silicon nitride films on wafers according to claim 2 wherein said cleaning gas comprises  $\text{NF}_3$ .

Claim 5 (Canceled)

10 Claim 6 (Original) The process for depositing silicon nitride films on wafers according to claim 1 wherein said nitrogen-containing gas comprises ammonia gas.

15 Claim 7 (Original) The process for depositing silicon nitride films on wafers according to claim 1 wherein silicon nitride deposition process is carried out at a temperature of between 450~600°C.

Claim 8 (Original) The process for depositing silicon nitride films on wafers according to claim 1 wherein said BTBAS is flowed into said tube at a flow rate of about 25~500 sccm.

20 Claim 9 (Original) The process for depositing silicon nitride films on wafers according to claim 1 wherein said nitrogen-containing gas is flowed into said tube at a flow rate of about 50~1000 sccm.

25 Claims 10-15 (canceled)